High Gain GaN Transistor supports Radar and Infrastructure

8/29/2019 – San Jose, California: RFMW announces design and sales support for a high gain, GaN transistor with excellent efficiency. The Qorvo QPD0050 spans DC to 3.6 GHz with 75 Watts of P3dB output power and maximum drain efficiency of 78%. Linear gain is 22 dB and efficiency-tuned P3dB gain is 19.4 dB. Designed for 48 V operation, the QPD0050 serves military & commercial radar, land mobile radio communications and test instrumentation. The device can be used in Doherty architecture for the final stage of small cells, microcells, and active antenna systems or, as a driver in a macrocell base station amplifier. Offered in a plastic overmold, SMT package.

Samples are available for qualified requirements through RFMW at 1-877-FOR RFMW (367-7369) within North America; or please find your local sales engineer (worldwide) at the contact page on the RFMW web site.

About RFMW

RFMW is a specialty electronics distribution company focused exclusively on serving customers that require RF and microwave components and semiconductors, as well as component engineering support. The company continues to expand its list of products from selective suppliers with RF/microwave expertise. RFMW deploys a highly experienced, technically skilled team to assist customers with component selection and fulfillment.

To learn more about RFMW, visit their Website at www.rfmw.com, or call us at 1.877.FOR.RFMW (367-7369), or via e-mail at info@rfmw.com.

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